III. Listing of Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) An integrated circuit package bond pad, comprising:

an insulating layer;

an electrode located over the insulating layer and having a first surface configured to be bonded to external circuitry and a second surface opposite the first surface; and

a plurality of conductive members located in the insulating layer, wherein ones of the plurality of conductive members contact the second surface of the electrode.

2. (Original) The bond pad of claim 1 wherein the electrode includes a plurality of discrete conductors separated by portions of a dielectric layer.

3. (Original) The bond pad of claim 1 wherein the plurality of conductive members each have a shape selected from the group consisting of:

a square cube;

a rectangular cube; and

a cylinder.

4. (Original) The bond pad of claim 1 wherein the plurality of conductive members each have a cross-shaped footprint.

5. (Original) The bond pad of claim 1 wherein at least two of the ones of the plurality of conductive members have a first size and at least two of the ones of the plurality of conductive members have a second size.

6. (Original) The bond pad of claim 1 wherein the ones of the plurality of conductive members are first ones each having a first shape, wherein second ones of the plurality of conductive members each have a second shape.

7. (Original) The bond pad of claim 1 wherein each of the plurality of conductive members comprises a material selected from the group consisting of:

metal;

doped polysilicon; and

metal silicide.

8. (Original) The bond pad of claim 1 wherein at least two of the plurality of conductive members are located in a portion of the insulating layer outside a perimeter of the electrode.

9. (Original) The bond pad of claim 1 wherein a volumetric ratio of the ones of the plurality of conductive members to the insulating layer ranges between about 1:1 and about 1:5.

10. (Original) The bond pad of claim 1 wherein the first surface of the electrode has a serrated thickness profile.

11. (Original) A method of manufacturing an integrated circuit package bond pad, comprising:

forming an insulating layer over a substrate;

forming a plurality of conductive members in the insulating layer; and

forming an electrode over the insulating layer, the electrode having:

a first surface configured to be bonded to external circuitry; and

a second surface opposite the first surface and contacting ones of the plurality of conductive members.

12. (Original) The method of claim 11 wherein forming the electrode includes forming a plurality of discrete conductors separated by portions of a dielectric layer.

13. (Original) The method of claim 11 wherein forming the plurality of conductive members includes depositing a material selected from the group consisting of:

metal;

doped polysilicon; and

metal silicide.

14. (Original) The method of claim 11 wherein the first surface of the electrode has a serrated thickness profile.

15. (Original) A method of manufacturing an electronic device, comprising:

providing a substrate having a first bond pad located thereon;

providing an integrated circuit package having a second bond pad located thereon, the second bond pad including:

an insulating layer;

an electrode located over the insulating layer and having a first surface configured to be bonded to the first bond pad and a second surface opposite the first surface; and

a plurality of conductive members located in the insulating layer, wherein ones of the plurality of conductive members contact the second surface of the electrode; and

forming a bond electrically coupling the first and second bond pads.

16. (Original) The method of claim 15 wherein the electrode includes a plurality of discrete conductors separated by portions of a dielectric layer.

17. (Original) The method of claim 15 wherein the plurality of conductive members each have a rectangular cube shape.

18. (Original) The method of claim 15 wherein a volumetric ratio of the ones of the plurality of conductive members to the insulating layer ranges between about 1:1 and about 1:5.

19. (Original) The method of claim 15 wherein the first surface of the electrode has a serrated thickness profile.

20. (Original) The method of claim 15 wherein forming a bond includes a process selected from the group consisting of:

wire bonding; and

surface mounting.